



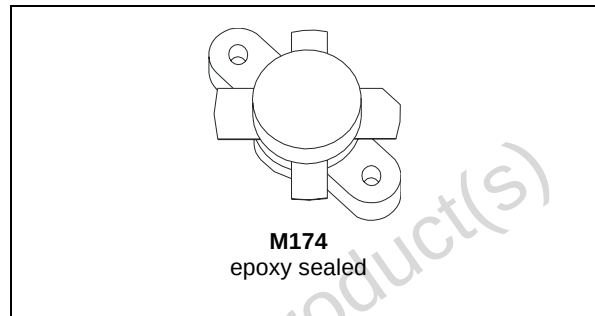
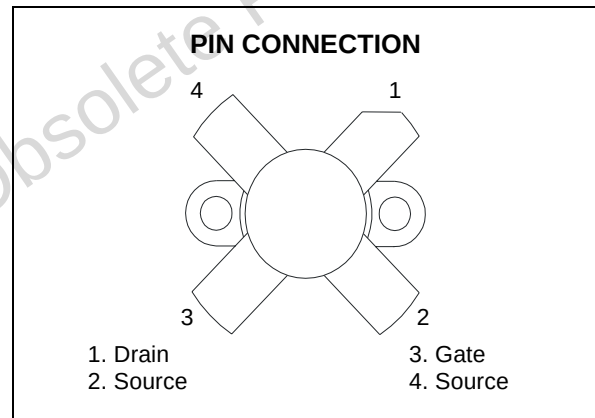
SD2931

RF POWER TRANSISTORS HF/VHF/UHF N-CHANNEL MOSFETs

- GOLD METALLIZATION
- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- $P_{OUT} = 150\text{ W MIN. WITH } 14\text{ dB GAIN @ } 175\text{ MHz}$

DESCRIPTION

The SD2931 is a gold metallized N-Channel MOS field-effect RF power transistor. It is intended for use in 50 V dc large signal applications up to 230 MHz.



ORDER CODES

Order Codes	Marking	Package	Packaging
SD2931	SD2931	M174	Plastic Tray

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25\text{ }^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain Source Voltage	125	V
V_{DGR}	Drain-Gate Voltage ($R_{GS} = 1\text{M}\Omega$)	125	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current	20	A
P_{DISS}	Power Dissipation	292	W
T_j	Max. Operating Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{th(j-c)}$	Junction -Case Thermal Resistance	0.6	$^{\circ}\text{C/W}$
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ELECTRICAL SPECIFICATION ($T_{CASE} = 25^{\circ}C$)

STATIC

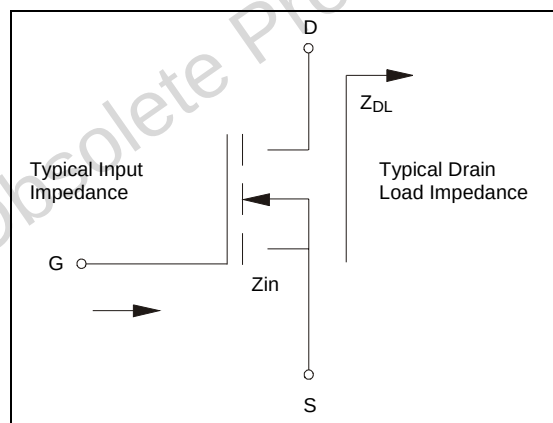
Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$	$I_{DS} = 100\text{ mA}$	125			V
I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 50\text{ V}$			50	μA
I_{GSS}	$V_{GS} = 20\text{ V}$	$V_{DS} = 0\text{ V}$			250	nA
$V_{GS(Q)*}$	$V_{DS} = 10\text{ V}$	$I_D = 250\text{ mA}$	1.5		4.0	V
$V_{DS(ON)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$			3.0	V
G_{FS}	$V_{DS} = 10\text{ V}$	$I_D = 5\text{ A}$	5			mho
C_{ISS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 50\text{ V}$		480		pF
C_{OSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 50\text{ V}$		190		pF
C_{RSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 50\text{ V}$		18		pF

* $V_{GS(Q)}$ sorted with alpha/numeric code marked on unit.

DYNAMIC

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
P_{OUT}	$V_{DD} = 50\text{ V}$	$I_{DQ} = 250\text{ mA}$ $f = 175\text{ MHz}$	150			W
G_{PS}	$V_{DD} = 50\text{ V}$	$I_{DQ} = 250\text{ mA}$ $P_{OUT} = 150\text{ W}$ $f = 175\text{ MHz}$	14	15		dB
η_D	$V_{DD} = 50\text{ V}$	$I_{DQ} = 250\text{ mA}$ $P_{OUT} = 150\text{ W}$ $f = 175\text{ MHz}$	55	65		%
Load Mismatch	$V_{DD} = 50\text{ V}$	$I_{DQ} = 250\text{ mA}$ $P_{OUT} = 150\text{ W}$ $f = 175\text{ MHz}$ All Phase Angles	10:1			VSWR

IMPEDANCE DATA



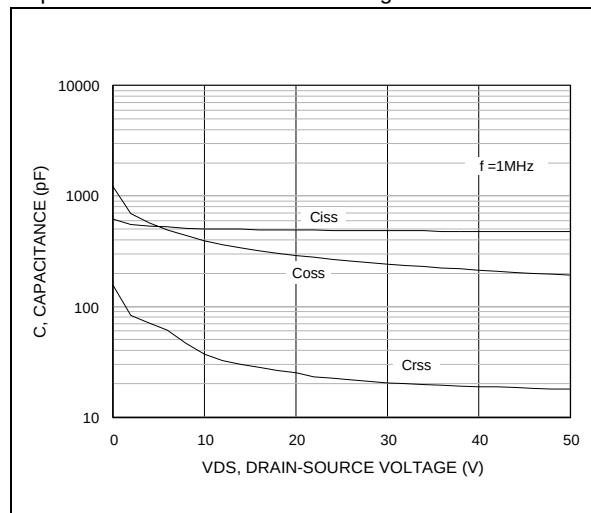
FREQ	$Z_{IN} (\Omega)$	$Z_{DL} (\Omega)$
30 MHz	$1.7 - j 5.7$	$6.8 + j 0.9$
175 MHz	$1.2 - j 2.0$	$2.0 + j 2.4$

 V_{GS} SORTS

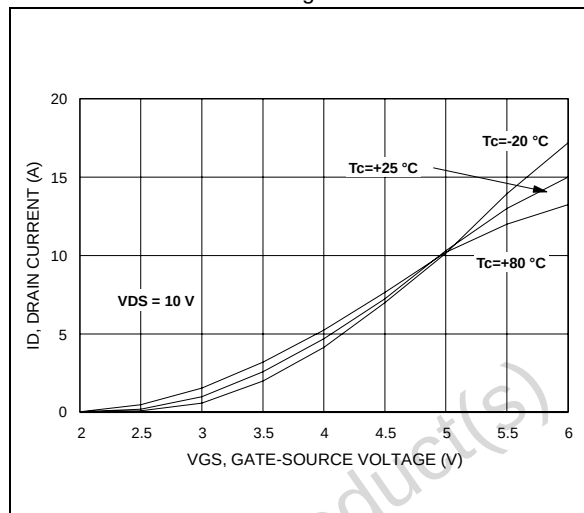
AA	1.5 - 1.6	J	2.8 - 2.9
BB	1.6 - 1.7	K	2.9 - 3.0
CC	1.7 - 1.8	L	3.0 - 3.1
DD	1.8 - 1.9	M	3.1 - 3.2
EE	1.9 - 2.0	N	3.2 - 3.3
A	2.0 - 2.1	P	3.3 - 3.4
B	2.1 - 2.2	Q	3.4 - 3.5
C	2.2 - 2.3	R	3.5 - 3.6
D	2.3 - 2.4	S	3.6 - 3.7
E	2.4 - 2.5	T	3.7 - 3.8
F	2.5 - 2.6	U	3.8 - 3.9
G	2.6 - 2.7	V	3.9 - 4.0
H	2.7 - 2.8		

TYPICAL PERFORMANCE

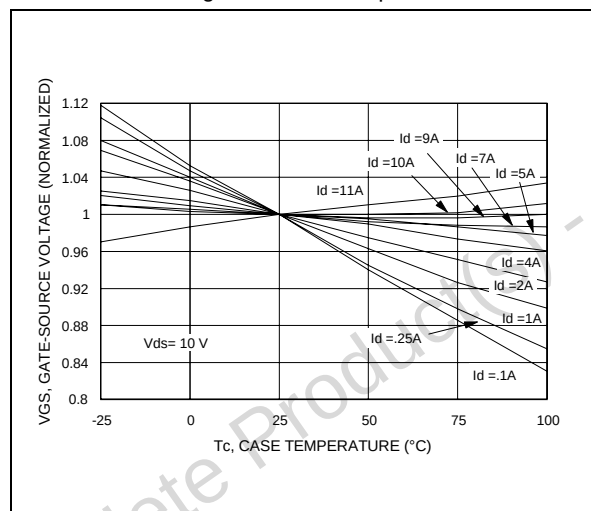
Capacitance vs. Drain-Source Voltage



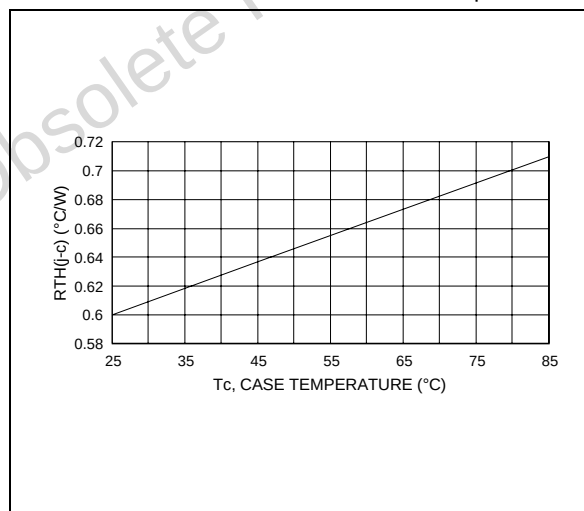
Drain Current vs. Gate Voltage



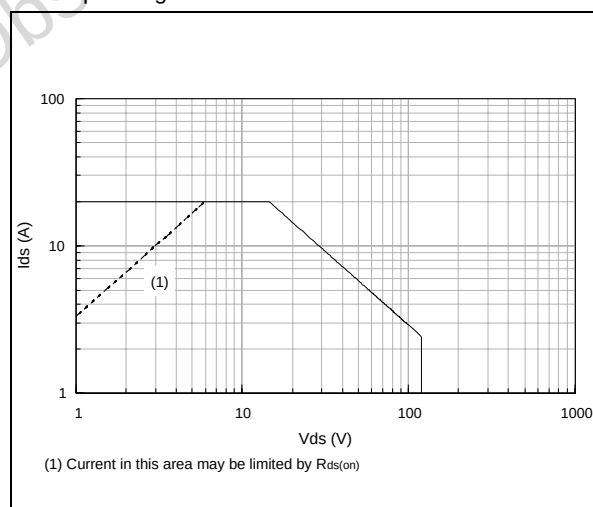
Gate-Source Voltage vs. Case Temperature



Maximum Thermal Resistance vs. Case Temperature

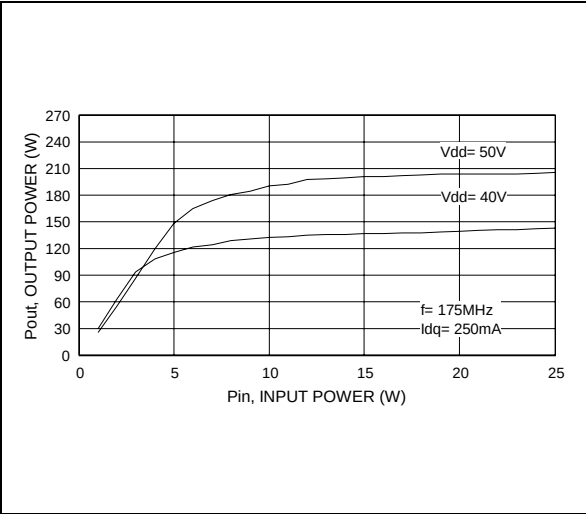


Safe Operating Area

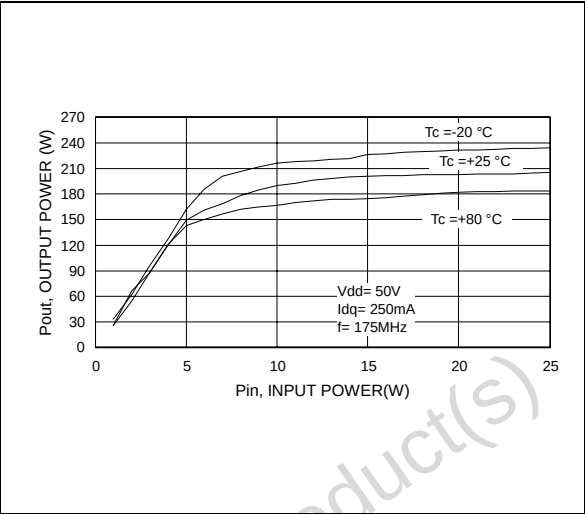


TYPICAL PERFORMANCE (175 MHz)

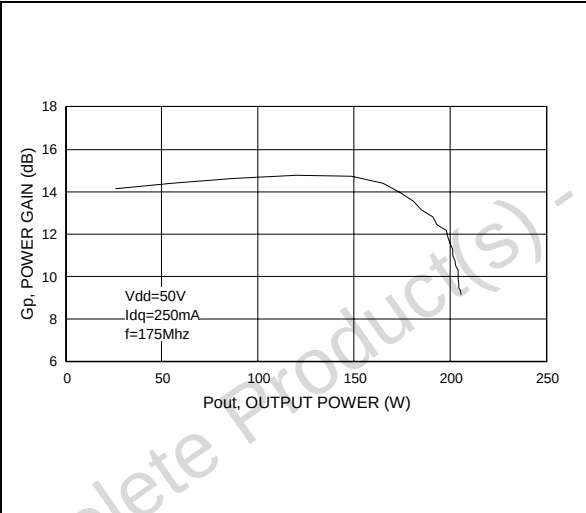
Output Power vs. Input Power



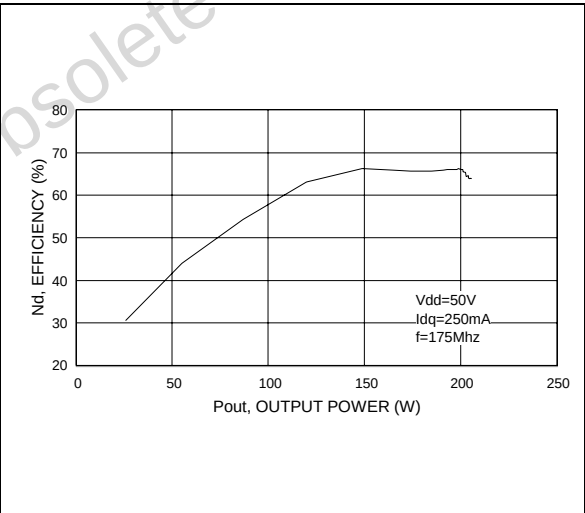
Output Power vs. Input Power



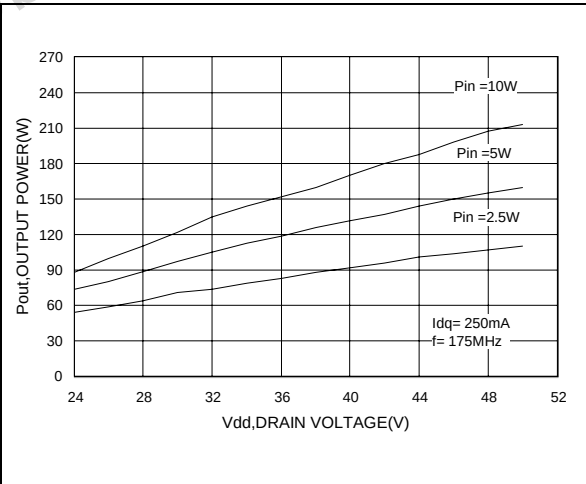
Power Gain vs. Output Power



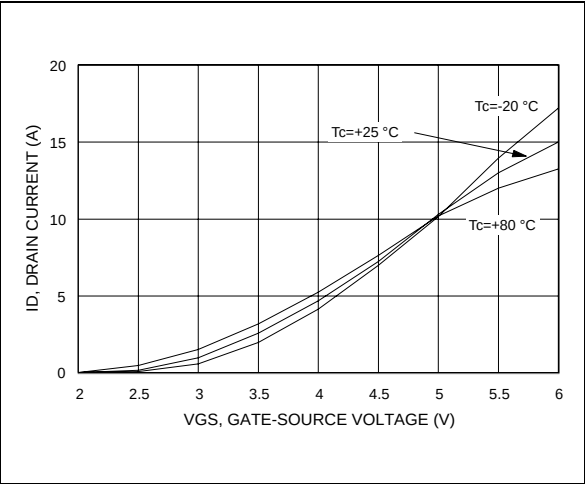
Efficiency vs. Output Power



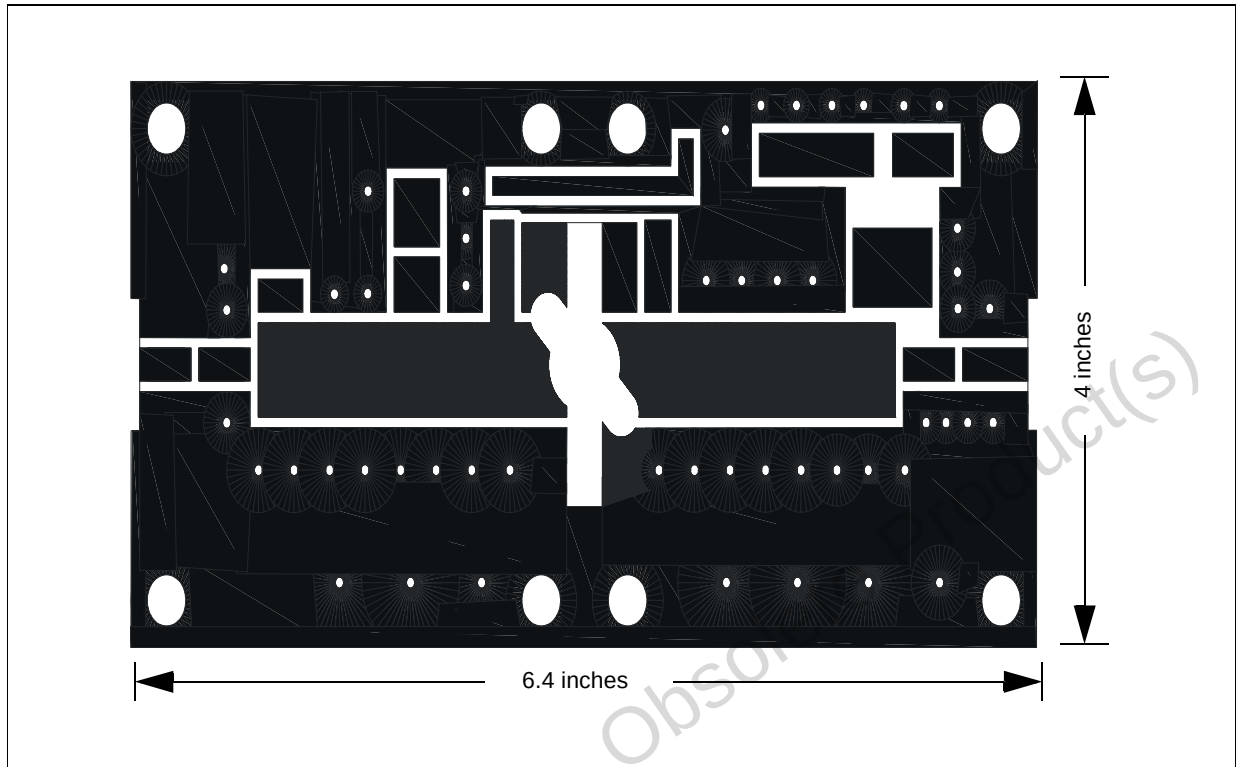
Output Power vs. Supply Voltage



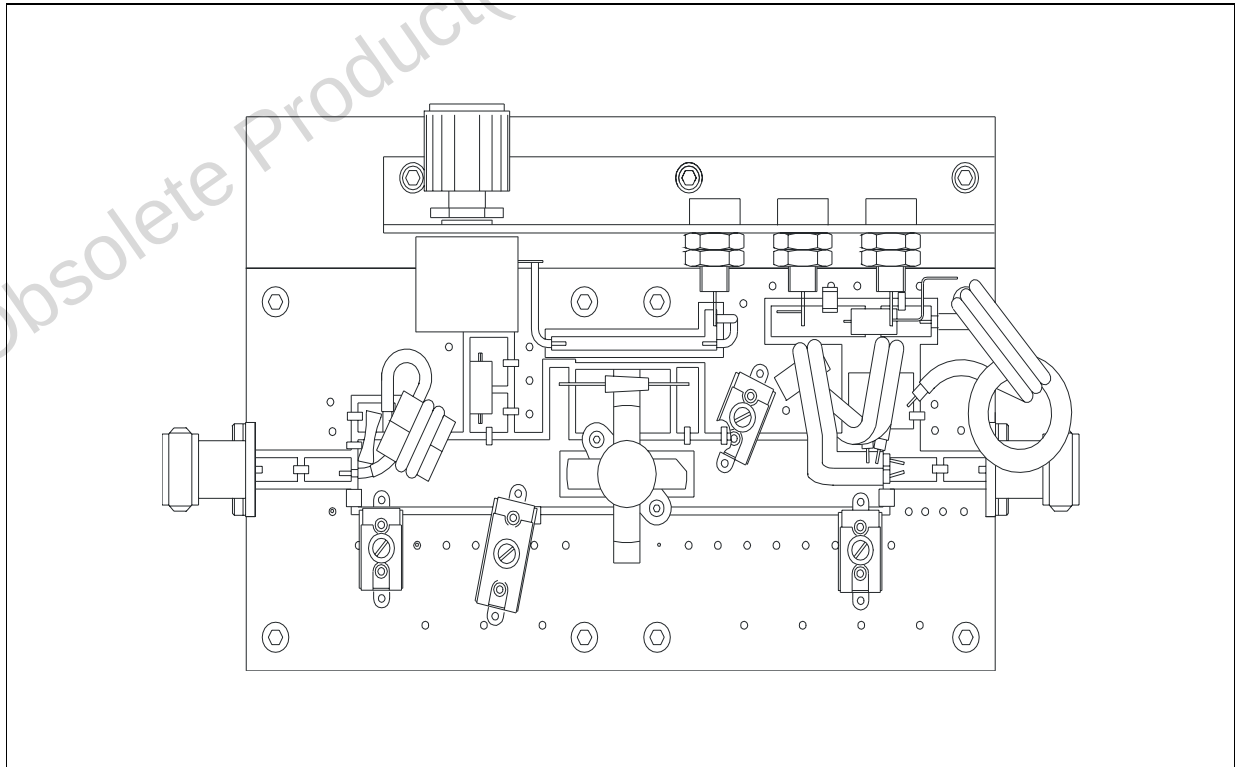
Drain Current vs. Gate-Source Voltage



175 MHz Test Circuit Photomaster

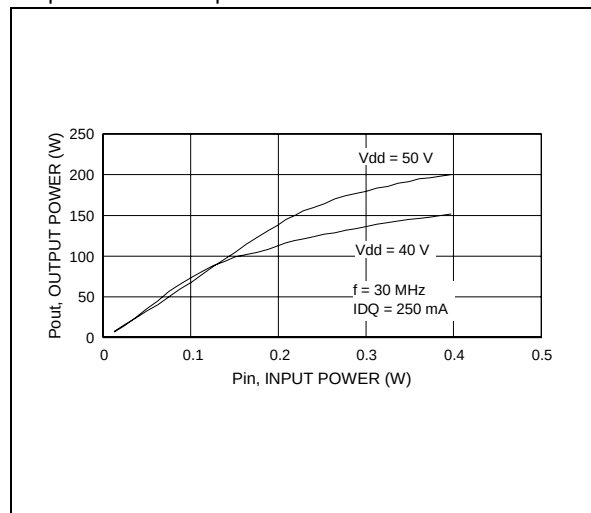


175 MHz Test Circuit

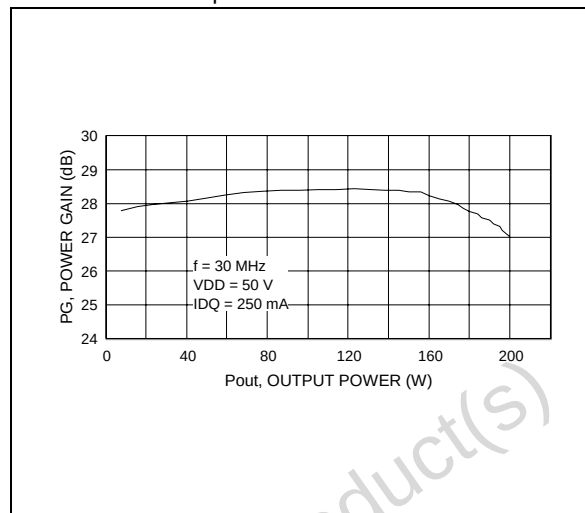


TYPICAL PERFORMANCE (30 MHz)

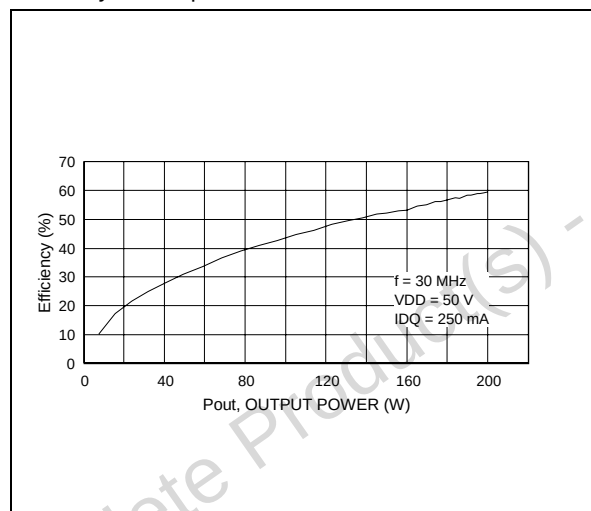
Output Power vs. Input Power



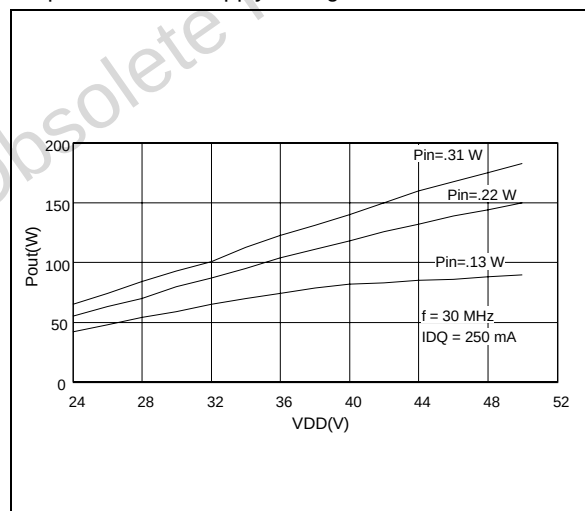
Power Gain vs. Output Power



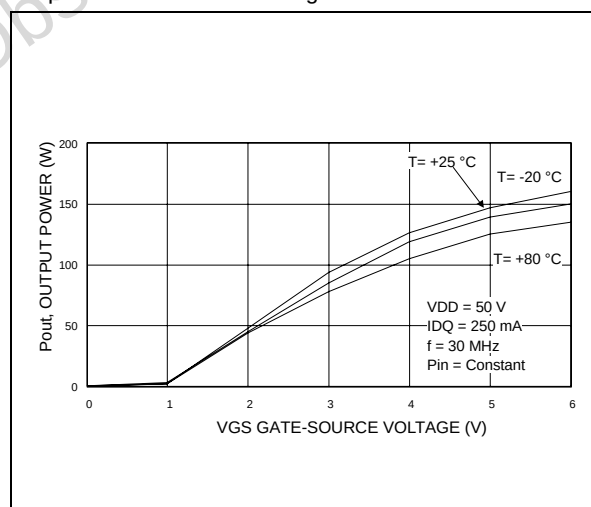
Efficiency vs. Output Power



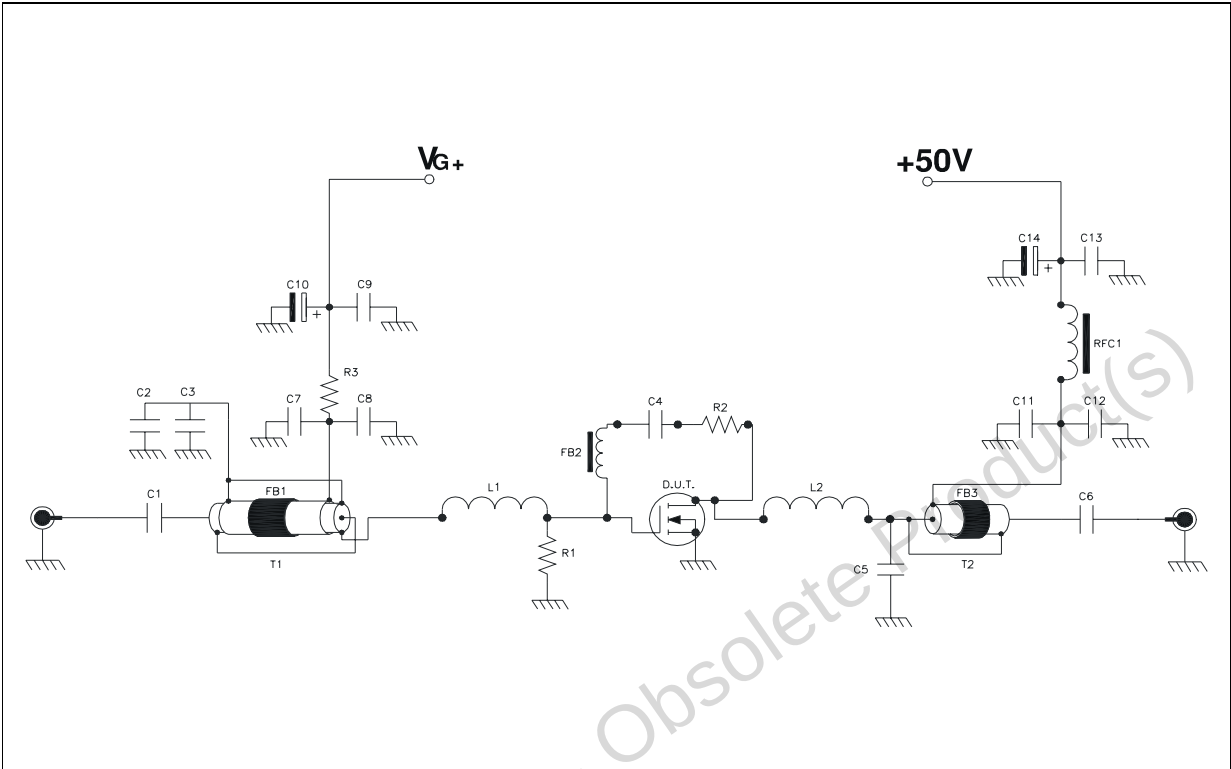
Output Power vs. Supply Voltage



Output Power vs. Gate Voltage



30 MHz Test Circuit Schematic (Engineering Test Circuit)

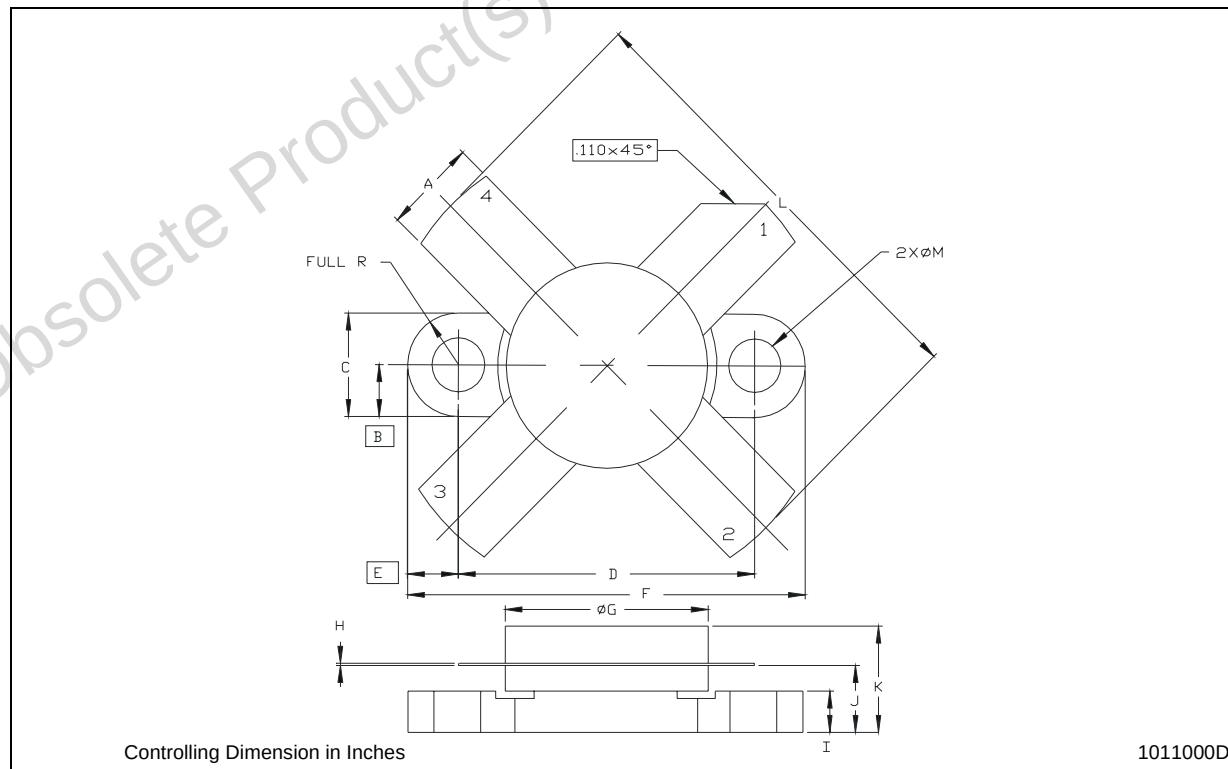


30 MHz Test Circuit Component Part List

T1	9:1 Transformer, 25 ohm Flexible Coax with extra shield .090 OD 15" Long
T2	1:4 Transformer, 50 ohm Flexible Coax .225 OD 15" Long
FB1	Toroid 1.7" OD .30" ID 220μ 4Turns
FB2	Surface Mount EMI Shield Bead
FB3	Toroid 1.7" OD .300" ID 220μ 3Turns
RFC1	Toroid 0.5" OD 0.30" ID 125μ 4Turns 12 awg wire
PCB	0.62" Woven Fiberglass, 1 oz. Copper, 2 Sides, εr = 2.55
R1, R3	1 K ohm 1 W Chip Resistor
R2	680 ohm 3W Wirewound Resistor
C1,C4,C6,C7,C8,C9, C11,C12,C13	0.1 μF ATC Chip Cap
C2,C3	750 pF ATC Chip Cap
C5	470 pF ATC Chip Cap
C10	10 μF 63 V Electrolytic Capacitor
C14	100 μF 63 V Electrolytic Capacitor

M174 (.500 DIA 4/L N/HERM W/FLG) MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A	5.56		5.584	0.219		0.230
B		3.18			0.125	
C	6.22		6.48	0.245		0.255
D	18.28		18.54	0.720		0.730
E		3.18			0.125	
F	24.64		24.89	0.970		0.980
G	12.57		12.83	0.495		0.505
H	0.08		0.18	0.003		0.007
I	2.11		3.00	0.083		0.118
J	3.81		4.45	0.150		0.175
K			7.11			0.280
L	25.53		26.67	1.005		1.050
M	3.05		3.30	0.120		0.130



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